

## NCE N-Channel Super Trench II Power MOSFET

### Description

The series of devices uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{DS(ON)}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.

### Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

### General Features

- $V_{DS} = 85V, I_D = 140A$   
 $R_{DS(ON)} = 3.4m\Omega$ , typical (TO-220)@  $V_{GS} = 10V$   
 $R_{DS(ON)} = 3.2m\Omega$ , typical (TO-263)@  $V_{GS} = 10V$
- Excellent gate charge x  $R_{DS(on)}$  product(FOM)
- Very low on-resistance  $R_{DS(on)}$
- 175 °C operating temperature
- Pb-free lead plating

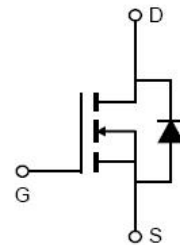
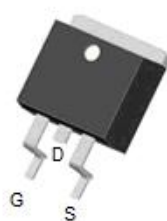
**100% UIS TESTED!**

**100%  $\Delta V_{ds}$  TESTED!**

TO-220



TO-263



Schematic Diagram

### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP040N85M	NCEP040N85M	TO-220	-	-	-
NCEP040N85MD	NCEP040N85MD	TO-263	-	-	-

### Absolute Maximum Ratings ( $T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	85	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	140	A
Drain Current-Continuous( $T_C = 100^\circ C$ )	$I_D(100^\circ C)$	105	A
Pulsed Drain Current	$I_{DM}$	560	A
Maximum Power Dissipation	$P_D$	200	W
Derating factor		1.33	W/ $^\circ C$
Single pulse avalanche energy (Note 1)	$E_{AS}$	1000	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 175	$^\circ C$

## Thermal Characteristic

Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.75	$^{\circ}\text{C/W}$
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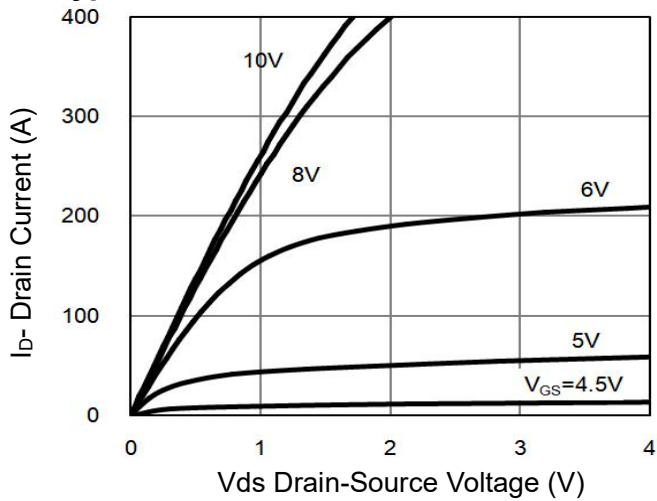
## Electrical Characteristics ( $T_c=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit	
Off Characteristics							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	85		-	V	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =85V, V <sub>GS</sub> =0V	-	-	1	μA	
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA	
On Characteristics							
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	2.0	3.0	4.0	V	
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =70A	TO-220	-	3.4	3.9	mΩ
			TO-263	-	3.2	3.9	mΩ
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =5V, I <sub>D</sub> =70A		90	-	S	
Dynamic Characteristics							
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =40V, V <sub>GS</sub> =0V, F=1.0MHz	-	4050	-	PF	
Output Capacitance	C <sub>oss</sub>		-	1000	-	PF	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	35	-	PF	
Switching Characteristics <small>(Note 2)</small>							
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =40V, I <sub>D</sub> =70A V <sub>GS</sub> =10V, R <sub>G</sub> =1.6Ω	-	17	-	nS	
Turn-on Rise Time	t <sub>r</sub>		-	10	-	nS	
Turn-Off Delay Time	t <sub>d(off)</sub>		-	37	-	nS	
Turn-Off Fall Time	t <sub>f</sub>		-	8	-	nS	
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =40V, I <sub>D</sub> =70A, V <sub>GS</sub> =10V	-	75	-	nC	
Gate-Source Charge	Q <sub>gs</sub>		-	17.7		nC	
Gate-Drain Charge	Q <sub>gd</sub>		-	25.5		nC	
Drain-Source Diode Characteristics							
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =70A	-		1.2	V	
Diode Forward Current	I <sub>S</sub>		-	-	140	A	
Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25°C, I <sub>F</sub> = 70A	-	72	-	nS	
Reverse Recovery Charge	Q <sub>rr</sub>	di/dt = 100A/μs	-	102	-	nC	

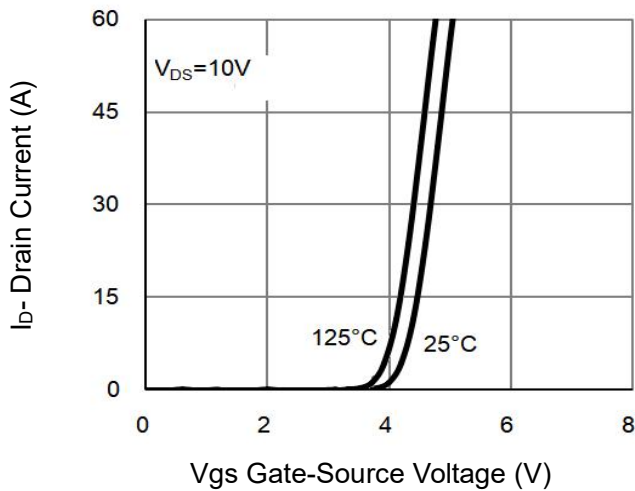
## Notes:

1. EAS condition :  $T_J=25^{\circ}\text{C}, V_{DD}=40V, V_G=-10V, L=0.5\text{mH}, R_G=25\Omega$
2. Guaranteed by design, not subject to production
3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of  $T_J(\text{MAX})=175^{\circ}\text{C}$ . The SOA curve provides a single pulse rating.

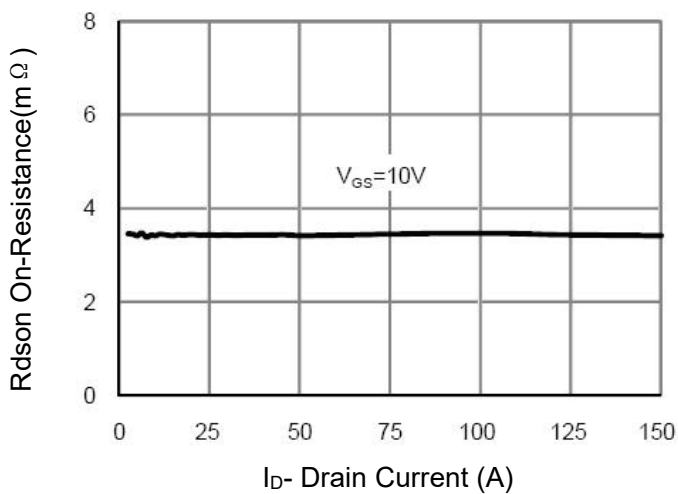
## Typical Electrical and Thermal Characteristics



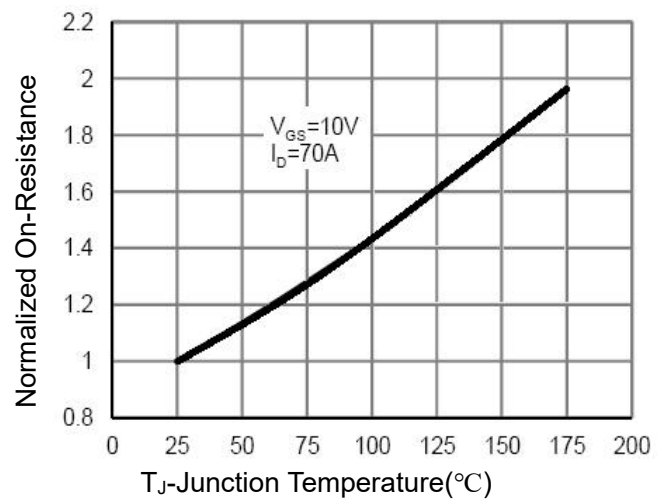
**Figure 1 Output Characteristics**



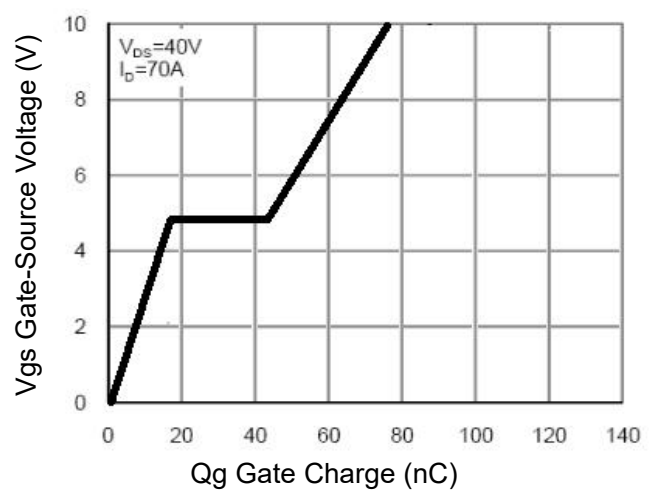
**Figure 2 Transfer Characteristics**



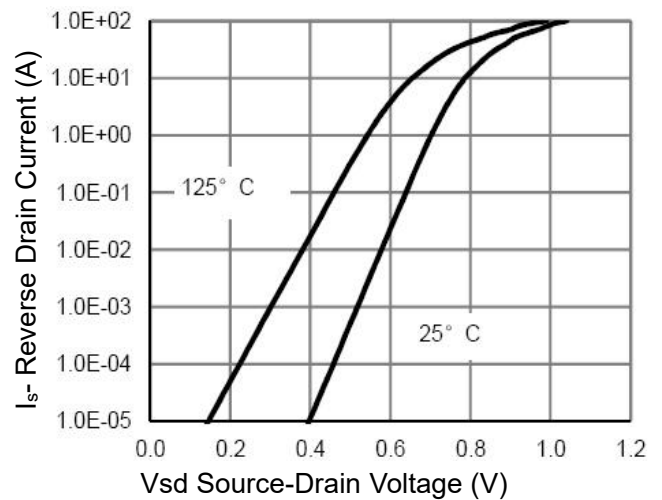
**Figure 3  $R_{DS(on)}$ - Drain Current**



**Figure 4  $R_{DS(on)}$ -Junction Temperature**



**Figure 5 Gate Charge**



**Figure 6 Source- Drain Diode Forward**

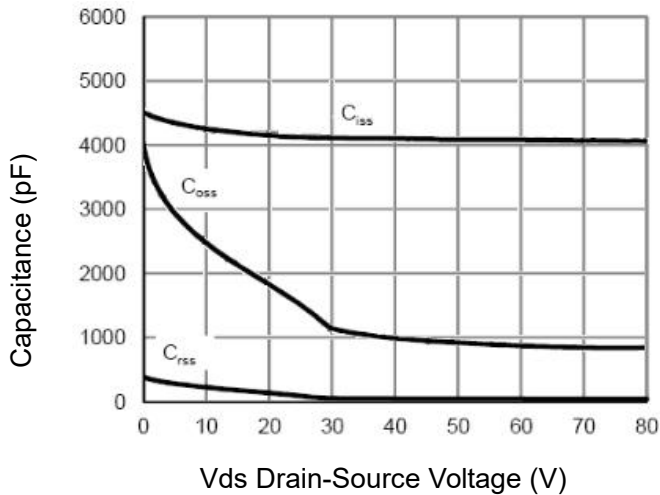


Figure 7 Capacitance vs Vds

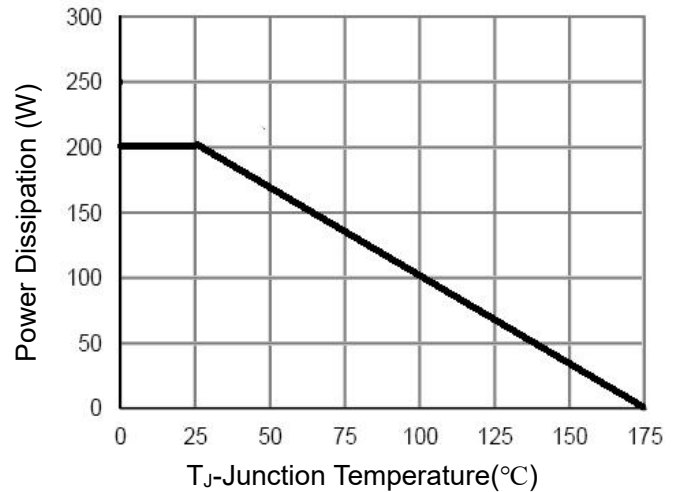


Figure 9 Power De-rating

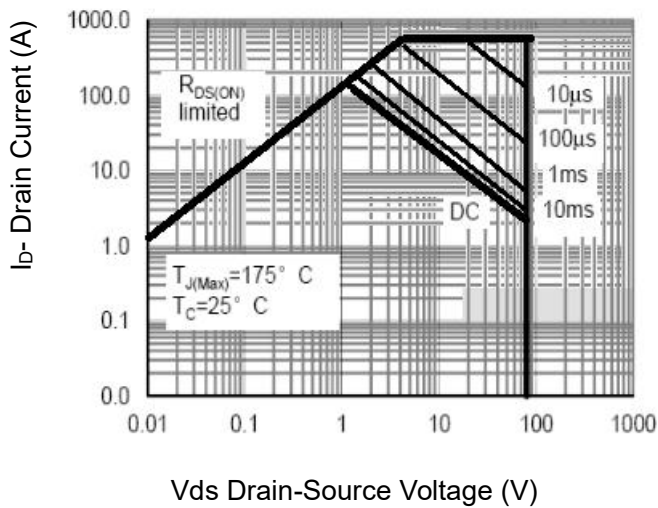


Figure 8 Safe Operation Area (Note3)

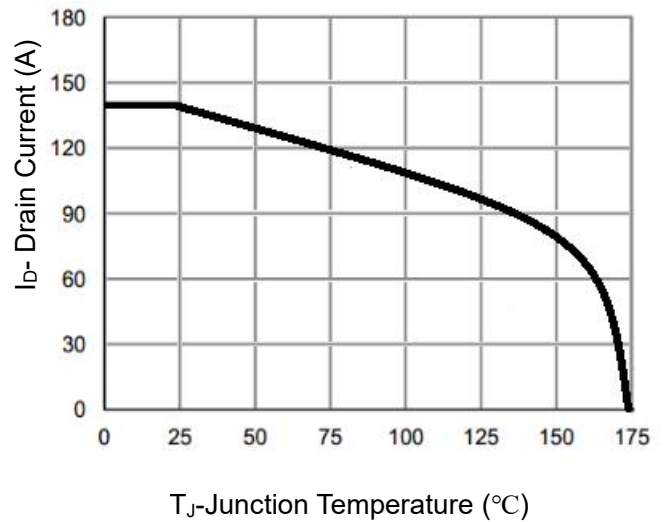


Figure 10 Current De-rating

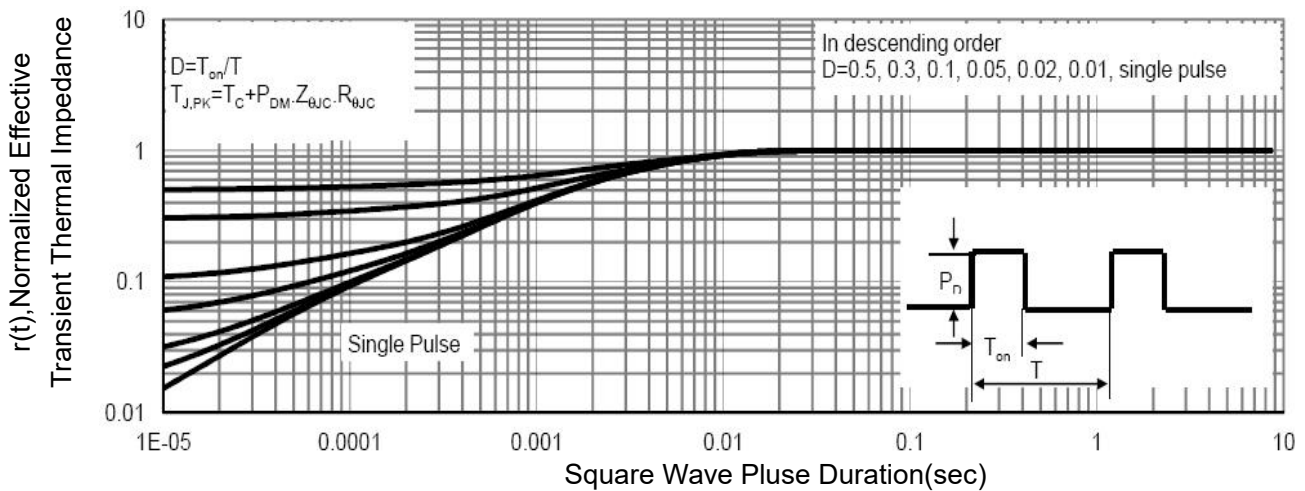
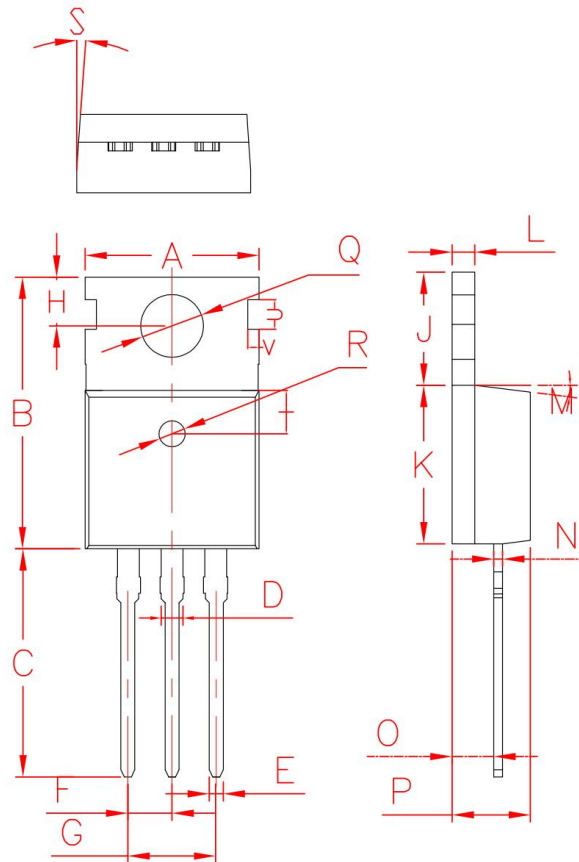


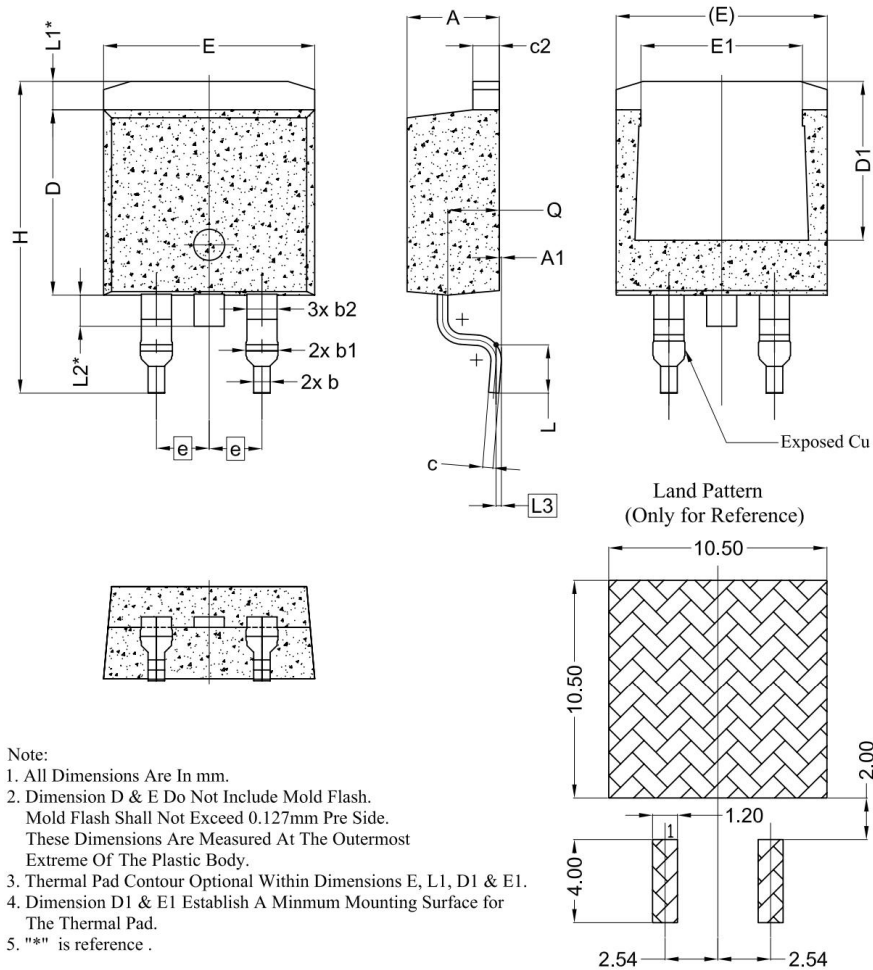
Figure 11 Normalized Maximum Transient Thermal Impedance

## TO-220-3L Package Information



Symbol	Min	Non	Max
A	9.80	10.00	10.20
B	15.40	15.60	15.80
C	12.75	13.10	13.45
D	1.18	1.31	1.44
E	0.70	0.80	0.90
F	2.42	2.54	2.66
G	4.84	5.08	5.32
H	2.73	2.80	2.87
I	2.40	2.50	2.60
J	6.40	6.50	6.60
K	9.00	9.10	9.20
L	1.29	1.30	1.32
M	6.5°	7.0°	7.5°
N	0.48	0.50	0.56
O	2.35	2.4	2.5
P	4.4	4.5	4.7
Q	3.5	3.6	3.63
R	1.4	1.5	1.6
S	2°	2.5°	3°
U	1.65	1.75	1.85
V	0.58	0.68	0.78

## TO-263-3L Package Information



SYMBOL	DIMENSIONS		
	MIN.	NOM.	MAX.
A	4.24	4.44	4.64
A1	0.00	0.10	0.25
b	0.70	0.80	0.90
b1	1.20	1.55	1.75
b2	1.20	1.45	1.70
c	0.40	0.50	0.60
c2	1.15	1.27	1.40
D	8.82	8.92	9.02
D1	6.86	7.65	—
E	9.96	10.16	10.36
E1	6.89	7.77	7.89
e	2.54 BSC		
H	14.61	15.00	15.88
L	1.78	2.32	2.79
L1	1.36 REF.		
L2	1.50 REF.		
L3	0.25 BSC		
Q	2.30	2.48	2.70

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